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(54) Title: USING LASER BASED SYSTEM FOR MEAN OF SHAPING OF UNSINGULATED & SINGULATED DIES BY SUBSTRATE LATTICE MANIPULATION

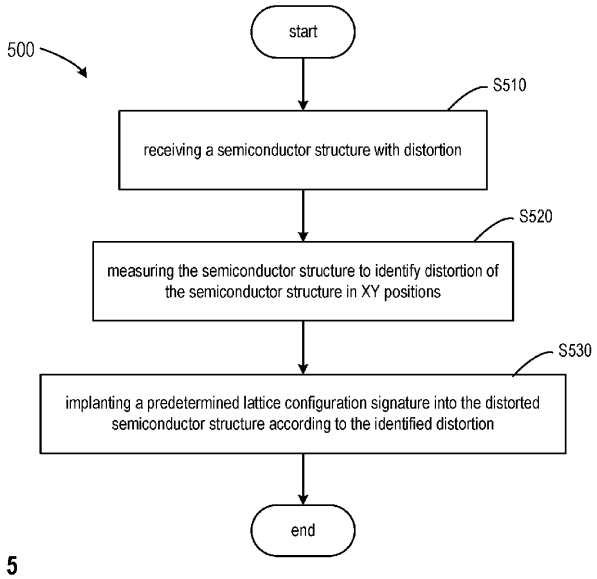


FIG. 5

(57) Abstract: Aspects of the present disclosure provide a method for correcting distortion of a semiconductor substrate. For example, the method can include receiving a semiconductor substrate with distortion, measuring the semiconductor substrate to identify the distortion in a plurality of positions on the semiconductor substrate, and implanting into the semiconductor substrate a lattice configuration signature according to the identified distortion in the positions such that the identified distortion of the semiconductor substrate is corrected.

[Continued on next page]

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